

Muon spin relaxation study of solute–vacancy interactions during natural aging of Al–Mg–Si–Cu alloys

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Abstract

Muon spin relaxation has the unique ability to detect very low concentrations of vacancies and vacancy–solute complexes in solids. In this work, we investigate quaternary Al–Mg–Si–Cu alloys and show that after quenching to room temperature from 848 K (575 °C), vacancies gradually become incorporated into clusters in the Al matrix. The total amount of vacancies in the material increases as small vacancy-rich clusters are formed, which is the opposite of the behavior in Cu-free Al–Mg–Si alloys.

Keywords: Aluminium alloys; Al-Mg-Si-Cu; Muon spin relaxation; Atomic clustering; Vacancies

19 Age-hardenable aluminium alloys are strengthened by nanometer-sized atomic clusters and precipitates that are
20 coherent with the aluminium matrix. These are formed by the segregation of atoms (e.g. Mg and Si), from a solid
21 solution where the solute atoms occupy substitutional sites in fcc-Al. Such a solid solution comprising a few % of
22 alloying elements is achieved by solution heat treatment (SHT) – an annealing step in the range 773–873 K (500–
23 600 °C). The solid solution is highly unstable after rapid cooling from SHT. During further lower-temperature heat
24 treatments (artificial aging) and even room temperature storage (natural aging), vacancies and solute atoms co-diffuse
25 and order to produce atomic clusters, still with all atoms at fcc-Al positions [1-3]. In Al–Mg–Si (6xxx) alloys, this
26 process is extremely complicated and consist of many distinct stages happening over a wide range of time scales,
27 from seconds to years [4-6]. Minor additions of certain elements to the alloy composition can modify the properties
28 of the alloy. The most important quaternary element in an industrial context is copper, as it enhances the precipitate
29 nucleation and increases the hardness in Al–Mg–Si alloys. New types of precipitate phases are also formed with the
30 introduction of Cu [7-9], and Cu has been found to suppress the detrimental effect of room temperature storage
31 between SHT and artificial aging [4, 10-11].

32 The most important techniques to detect and quantify precipitates in the 6xxx system has been transmission electron
33 microscopy (TEM) and atom probe tomography (APT). However, small atomic clusters are difficult to detect in TEM,
34 APT is not suitable to investigate the crystallography of precipitates, and neither technique can map the presence of
35 vacancies. Studying the microstructure shortly after quenching from SHT is also very challenging with these
36 techniques, and requires sophisticated approaches [12]. Therefore, despite being a well-studied system, the clustering
37 and precipitation in Al–Mg–Si alloys poses many unanswered questions which require unconventional techniques to
38 be answered.

39 Muon spin relaxation (μ SR) is one such technique, which relies on the production of exotic particles (positive muons)
40 for investigating short-range magnetic fields and the presence of point defects in solids. When a high-energy muon
41 enters a sample of aluminium, it is thermalized in a few picoseconds, and proceeds to diffuse interstitially inside the
42 sample. If the muon is trapped at a certain site and therefore stationary, the magnetic dipole interaction between the
43 magnetic moment of the muon and the nuclear magnetic moment of ^{27}Al causes precession of the muon spin, and in
44 time the gradual depolarization (relaxation) of an ensemble of muon spins [13-14]. The relaxation rate gives us
45 information on the particular trapping site and the trapping–detrapping kinetics, enabling the identification of various
46 point defects in differently heat-treated alloy samples. This work builds upon earlier literature on aluminium with
47 trace elements and Al–Mg–Si alloys and extends the analysis to the same alloys with Cu additions. The Al–Mg–Si–
48 Cu alloys show a surprising muon trapping behavior that does not occur without all three alloying elements present.
49 This discovery helps to further our understanding of the vacancy and clustering kinetics during natural aging in Al–
50 Mg–Si(–Cu) alloys.

51 The materials used in this study were prepared by melting pure Al (purity 99.99 %) with Si and Mg (purity 99.9 %) and Cu (purity 99.99 %) in air. The resulting ingots were formed into 1.0 mm thick plates by hot and cold rolling. Several pieces of the samples were cut out from the plate with the approximate dimensions $1.0 \times 25 \times 25 \text{ mm}^3$. The

54 chemical compositions and heat treatment temperatures/periods are described in Table 1. All the samples underwent
55 a SHT at 848 K (575 °C) for 1 hour and a subsequent quenching in ice water. After quenching, three kinds of
56 treatments were employed:

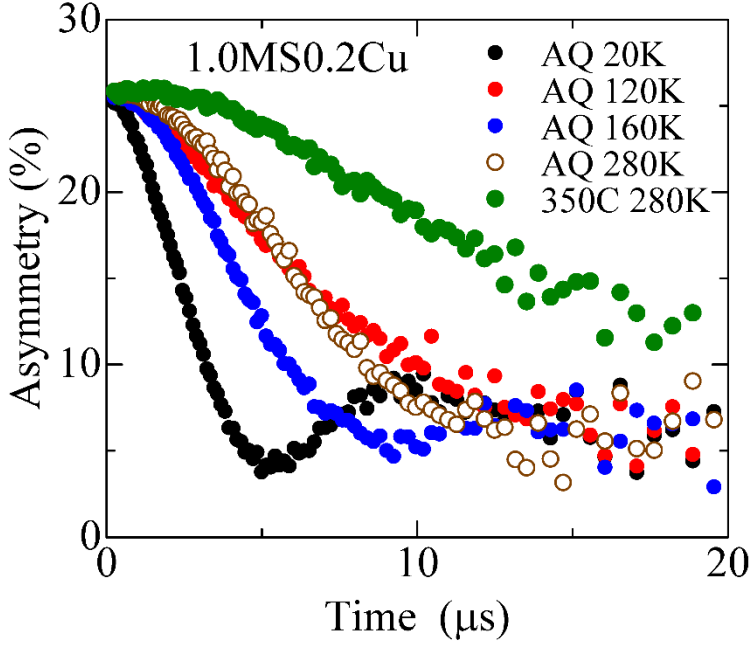
- 57 1. The μ SR measurement started immediately after quenching from SHT (within approximately 15 min). The
58 datasets with this process are denoted *-AQ.
- 59 2. Samples were stored at room temperature for a number of days before the measurement (denoted as *-...d).
- 60 3. Immediately after quenching, samples were annealed at a given temperature in the range 373–623 K (100–
61 350 °C) for a time required to stabilize the precipitate microstructure (noted as *-...C).

62
63 Since the base aluminum used in this study contains a few ppm of trace elements such as Si, Fe, Cu, Mn and Mg, we
64 also measured the temperature dependence of μ SR spectra with base Al to estimate the background trapping rate
65 level from impurities.

66 The μ SR experiments were carried out at the RIKEN-RAL Muon Facility at the Rutherford–Appleton laboratory
67 [15]. A pulsed positive muon beam is produced via the decay of positive pions, which are a product of nuclear
68 reactions between a carbon target and high-energy protons from the ISIS synchrotron. The muons are 100% spin
69 polarized antiparallel to their velocity. Each muon decays into a positron and two neutrinos. The emission direction
70 of the positron is asymmetric with respect to the muon spin. The probability of emission in a certain direction is $P(\theta)$
71 $= 1 + A \cos(\theta)$, in which θ is the angle between the positron direction and the muon spin, and A is an asymmetry
72 parameter. We used the ARGUS muon spectrometer, which detects positrons in the forward and backward direction
73 with respect to the incoming muon beam. From this we obtain the degree of muon spin relaxation (or simply
74 *asymmetry*) as a function of time spent inside the material before decaying.

75 Since muon kinetics vary greatly with temperature, a helium flow cryostat was used to control the temperature of the
76 samples. Temperature series were acquired, with 20 to 60 million positron counts (events) recorded at each
77 temperature point in the range 20–300 K (–253 to +27 °C). In isothermal measurements, as quenched (AQ) samples
78 were kept at 280 K (7 °C), and 10 million positron counts were recorded at each time step to monitor the time
79 evolution of spin relaxation rate of the samples. This was done to capture the vacancy and clustering kinetics, which
80 occurs at a suitably slow rate somewhat below room temperature.

81 We have interpreted the measured relaxation spectra using a Monte Carlo simulation, in which four fitting parameters
82 were employed: the dipolar width (Δ), trapping rate (ν_t), detrapping rate (ν_d), and fraction of initially trapped muons
83 (P_0) [13, 16]. This method has been introduced in the literature [17-18]. An ensemble of 60 million muons are
84 simulated to produce a five-dimensional relaxation function $f(\Delta, \nu_t, \nu_d, P_0, t)$, in which a muon spin is assumed to
85 depolarize only when it is trapped, but no relaxation occurs during diffusion (two state model). Simulated relaxation
86 functions are compared with the experimental ones to extract the best-fit parameters.



87

88 Figure 1: Example muon spin relaxation spectra for sample 1.0MS0.2Cu, showing spin asymmetry as a function of
 89 time spent inside the sample before muon decay.

90

91 Figure 1 shows the zero-field relaxation spectra observed for 1.0MS0.2Cu-AQ at measurement temperatures 20–280
 92 K (–253 to 7 °C) and for 1.0MS0.2Cu-350C at 280 K (7 °C). The horizontal axis denotes the time (t) from a muon
 93 pulse was injected into the sample until the muon decay. The plot demonstrates that the muon spin depolarization
 94 rate depends heavily on temperature. The spectrum for 1.0MS0.2Cu-AQ at 20 K (–253 °C), where the kinetics are
 95 very slow, has a typical shape described by the Kubo–Toyabe function [19]:

$$96 \quad G(t) = \frac{1}{3} + \frac{2}{3}(1 - \Delta^2 t^2)e^{-\frac{1}{2}\Delta^2 t^2}, \quad (1)$$

97 where Δ is the dipolar width. This function yields a minimum at $t = \sqrt{3}/\Delta$ and subsequent increase to an asymptotic
 98 asymmetry value. Assuming a simple magnetic dipole interaction between an aluminum nucleon ^{27}Al and a muon, Δ
 99 can be described as [20-21]:

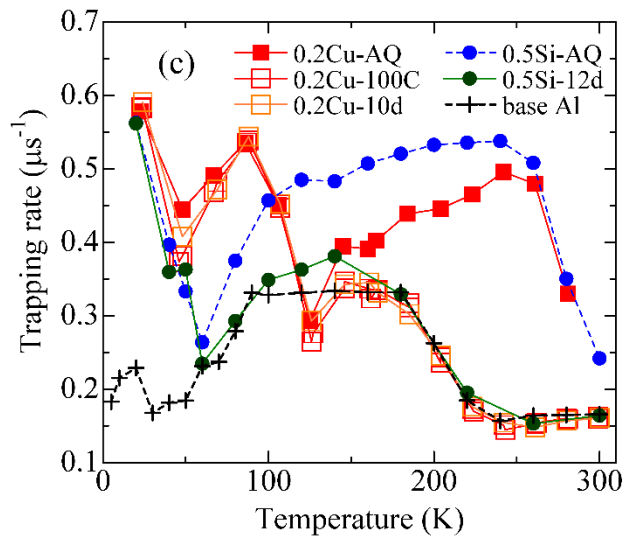
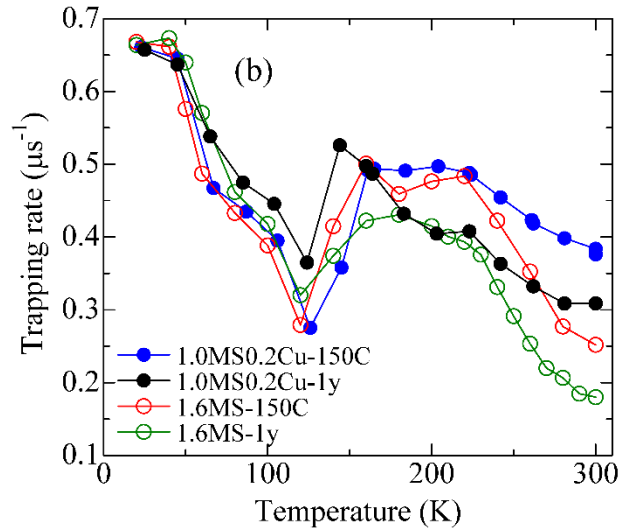
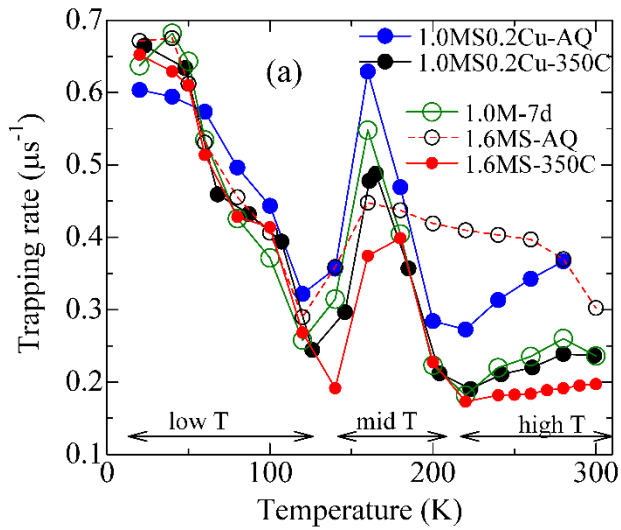
$$100 \quad \Delta^2 = \left(\frac{\mu_0}{4\pi}\right)^2 I(I+1) \left(\hbar\gamma_{\text{Al}}\gamma_{\mu}\right)^2 \frac{4}{9} \sum_i r_i^{-6}, \quad (2)$$

101 where $I = 5/2$ is the nuclear spin of ^{27}Al , $\gamma_{\text{Al}} = 6.98 \times 10^7$ rad/sT and $\gamma_{\mu} = 8.52 \times 10^8$ rad/sT are the gyromagnetic
 102 ratios of ^{27}Al and muon, respectively, and r_i is the distance between the muon and all nearby ^{27}Al nuclei. If a muon
 103 is trapped at a tetrahedral site, this results in a Δ value of $0.49 \mu\text{s}^{-1}$, while in an octahedral site, the Δ value is 0.38
 104 μs^{-1} . These values are approximate and based on a rigid Al lattice: For exact values, the repulsion between the muon

105 and all surrounding atoms must be taken into account. In Al–Mg–Si(–Cu) alloy samples, Al nuclei dominate the
106 dipole field which causes the muon spin relaxation, while contributions from Mg and Si nuclei are negligibly small,
107 since naturally abundant ^{24}Mg and ^{28}Si nuclei have no magnetic moment. The naturally abundant ^{63}Cu and ^{65}Cu have
108 comparable nuclear magnetic moments with that of ^{27}Al , therefore zero-field muon spin relaxation spectra in pure
109 copper showed a Δ value of approximately $0.39 \mu\text{s}^{-1}$ [22]. In this sense, a larger Δ value means that the muon is
110 surrounded by a higher number of Al/Cu atoms. The relaxation speed, however, depends not only on Δ , but on the
111 trapping, detrapping and diffusion rates of muons, which are dependent on the concentration of defects (e.g.
112 vacancies), their binding energy with muons, and temperature.

113 Figure 1 further shows that the depolarization for 1.0MS0.2Cu-AQ at 120 K ($-153 \text{ }^\circ\text{C}$) is slower than that at 160 K
114 ($-113 \text{ }^\circ\text{C}$), and the depolarization for 1.0MS0.2Cu-AQ at 280 K ($7 \text{ }^\circ\text{C}$) is faster than that for 1.0MS0.2Cu-350C at
115 280 K (7 °), reflecting a shift towards deeper traps with lower number densities as the temperature increases. Similar
116 relaxation spectra were acquired for all samples listed in Table 1, and fit to simulated spectra, as described in section
117 2.

118 The fitting results of the trapping rates (ν_t) for the samples are plotted as a function of temperature in Figure 2. The
119 temperature variations of ν_t in Figure 2(a) verify the three regions: 1) a low T region of 20–120K (-253 to $-153 \text{ }^\circ\text{C}$),
120 2) a mid T region of 140–200 K (-133 to $-73 \text{ }^\circ\text{C}$) and 3) a high T region of 220–300K (-53 to $+27 \text{ }^\circ\text{C}$). In the low T
121 region, it is known that muons are trapped in shallow electrical potentials produced by atoms in solid solution,
122 primarily Mg [13, 16, 23-24]. This is evident from the fact that the ν_t variation for 1.0Mg-10d resemble quite well
123 those of the other samples at low T . The fitted Δ values at 20 K ($-253 \text{ }^\circ\text{C}$) for all the samples in Figure 2(a) were
124 found to be approximately $0.35 \mu\text{s}^{-1}$, similar to the measurement by Hatano et al. [17]. With one solute atom next to
125 the muon, Eq. 2 matches the measurement for either a tetrahedral or octahedral site depending on its influence on the
126 surrounding atom positions. The chemical properties of a positive muon are similar to that of a proton (hydrogen ion).
127 A recent density functional theory calculation has proposed that a hydrogen prefers to be in the tetrahedral site in
128 aluminum [25]. Therefore, muons are also expected to be trapped in the tetrahedral sites.



129

130

131 Figure 2: Best-fit trapping rates for relaxation spectra acquired at increasing temperatures from 20 K to 300 K
 132 (−253 °C to +27 °C). (a) The Al–Mg–Si(–Cu) alloy as quenched and aged at 623 K (350 °C), as well as binary (Al–
 133 Mg) and ternary (Al–Mg–Si) alloy samples for reference. (b) Al–Mg–Si(–Cu) samples thermally aged at 423 K
 134 (150 °C) and room temperature stored for 1 year. (c) Binary Al–Cu and Al–Si alloys, and pure aluminium.

135

136 In the mid T region, a sharp trapping rate peak at 160 K (−113 °C) emerged for 1.0MS0.2Cu-AQ, -350C and 1.0Mg-
 137 7d. This peak is most likely associated with small Mg clusters, since 1.0Mg-10d contains only dissolved Mg atoms.
 138 The electrical potentials produced by single dissolved Mg atoms are too shallow to trap muons in this T region. The
 139 fitted Δ values for 1.0MS0.2Cu at 120 K and 160 K (−153 and −113 °C) were found to assume the same value of
 140 $0.26 \mu\text{s}^{-1}$. This Δ value, further decreased from that of pure Al, means that the muon is trapped by a complex of solute
 141 atoms/vacancies. The peak at 160 K (−113 °C) appears more strongly in the Al–Mg–Si–Cu alloy than in the ternary
 142 Al–Mg–Si alloy, which may be explained as follows: Through the precipitation sequence, we find more Si-rich

143 phases when Cu is added. This is exemplified by the equilibrium phases present in the samples annealed at 350 °C
144 (623 °C), which are mainly β -Mg₂Si for 1.6MS and Q-Mg₈Si₇Al₄Cu₂ for 1.0MS0.2Cu. If all available Si goes into
145 Q particles in 1.0MS0.2Cu-350C, the matrix still contains 0.28 at.% Mg and 0.10 at.% Cu, which can still form small
146 clusters.

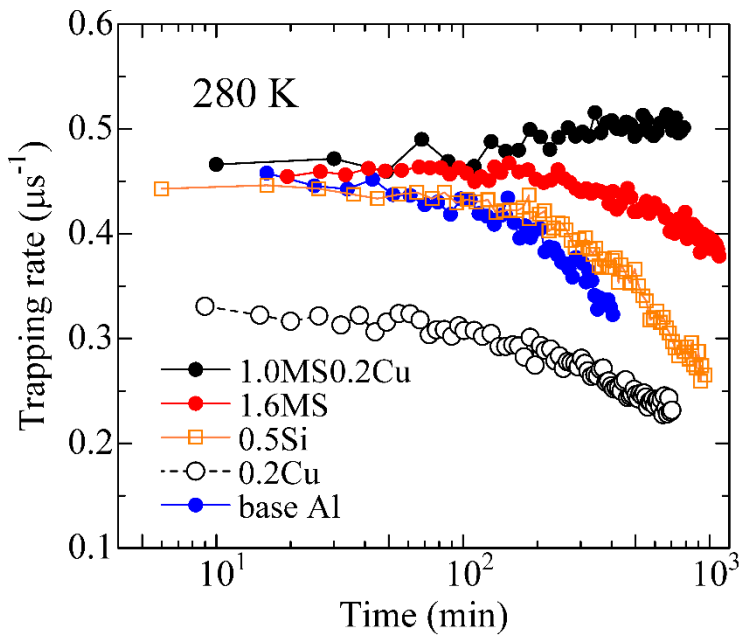
147 In the high *T* region, the ν_t of the as quenched samples are the largest, whereas those of samples annealed at high
148 temperatures are the smallest. In this region, muons are mainly trapped by vacancies, possibly bound to solute atoms
149 [17]. The ν_t values of 1.0MS0.2Cu-AQ are smaller than those of 1.6MS-AQ in the high *T* region, but the measurement
150 points at the highest temperatures seem to indicate 1.0MS0.2Cu-AQ will take over with a higher trapping rate at 300
151 K (27 °C) and above. Following our earlier interpretation [16], the Cu-free alloy has a higher number density of
152 solute clusters (trapping muons at 150–250 K (–123 to –23 °C)), while the Cu-added alloy has a higher number
153 density of vacancies (trapping muons above 250 K (–23 °C)). It has been widely noticed that Cu addition to Al–Mg–
154 Si alloys delay the precipitation processes, especially in the early stage of natural aging [26–28]. Even in the as
155 quenched condition, the two samples were exposed to natural aging for 10–15 minutes, during which the cluster
156 formation (especially Si–vacancy complex formation) proceeds with a lower speed if the Cu concentration is higher.

157 The artificial aging and long-term natural aging effects on ν_t are seen for 1.0MS0.2Cu and 1.6MS in Figure 2(b). In
158 the high-temperature region (above 200 K (–73 °C)), 1.0MS0.2Cu have higher trapping rates than its Cu-free
159 counterpart. Adding Cu has the effect of retaining a high number density of vacancies in the material even after
160 annealing or long-time room temperature storage. A rebalancing at medium temperature is also occurring: From the
161 as-quenched conditions in Figure 2(a), the sharp peak at 160 K (–113 °C) (Mg atoms/clusters) is replaced by a broader
162 peak at 140–220 K (–133 to –53 °C) (larger solute-vacancy clusters). This broad peak is already present in 1.6MS-
163 AQ, which means the early clustering kinetics is significantly faster in the Cu-free alloy. This phenomenon has been
164 observed before and explained by the large binding energy between Cu and vacancies, and the small diffusivity of
165 Cu in aluminum [26]. A delayed clustering process in Cu added samples eventually lead to a high number density of
166 small size clusters. It is worth to mention that the ν_t values for 1.0MS0.2Cu-150C and -1y decreases with
167 measurement temperature in an almost parallel manner above 200 K (–73 °C), and the same is valid for 1.6MS.

168 The temperature dependences of ν_t for the binary alloys displayed in Figure 2(c) are rather different from those for
169 the ternary and quaternary alloys. For the 0.2Cu samples, the changes in trapping rate with heat treatment happens at
170 measurement temperatures above 120 K (–153 °C). There is a unique, constant trapping rate peak for Al–Cu at 80
171 K, which have been explained by (vacancy-free) Cu atom complexes trapping muons [29]. This is comparable to the
172 peak at 160 K (–113 °C) for Mg atoms seen in Figure 2(a). The high ν_t values at 20 K (–253 °C) for 0.2Cu and 0.5Si
173 are caused by single Cu/Si impurity atoms. Above 120 K (–153 °C), the large ν_t values of 0.2Cu-AQ are naturally
174 attributable to Cu–vacancy pairs and complexes. Both natural and artificial aging for Al–0.2% Cu completely
175 suppresses the high-temperature behavior, reducing the ν_t values to base Al levels. This heat treatment response is
176 similar to that of Al–0.5% Si, although the starting point is different: 0.5Si-AQ has an elevated trapping rate at lower
177 temperatures (down to 60 K (–213 °C)). The main result of Figure 2(c) is that vacancies are annealed out of Al–Cu

178 and Al–Si alloys if subjected to either natural or artificial aging. For Al–Mg, a higher temperature is required to
 179 achieve this [16], while in the binary and ternary alloys presented in Figures 2(a,b), the temperature must be high
 180 enough to dissolve coherent precipitates, around 623 K (350 °C) for the vacancies to be freed.

181 From previous μ SR studies, muons are considered to be trapped by single vacancies or vacancy–solute pairs near
 182 room temperature. The ν_t values, therefore in most cases, decreases with time during natural aging since excess
 183 vacancies are lost at imperfections, such grain boundaries, voids, surfaces, etc. The change in trapping rate during
 184 storage at 280 K (7 °C) after quenching was measured for 1.0MS0.2Cu, 1.6MS, 0.5Si, 0.2Cu and base Al, as shown
 185 in Figure 3. The horizontal axis denotes the time after quenching from SHT on a logarithmic scale. The ν_t values for
 186 1.6MS, 0.5Si, 0.2Cu and base Al decreases with time. The speed of the decrease is inversely correlated with the
 187 solute concentration, as is expected since muons have more defects to be trapped at and more time to undergo spin
 188 relaxation. The reason why the ν_t values of 0.2Cu start out lower than in the other alloys is unclear.



189
 190 Figure 3: Fitted trapping rates from isothermal relaxation spectra. Samples are quenched from SHT and kept at 280 K
 191 (7 °C) throughout the measurements. The trapping rates decrease with time for all alloys except the quaternary Al–
 192 Mg–Si–Cu alloy, which increases with time.

193
 194 The surprising result from the isothermal experiment is that the ν_t value for 1.0MS0.2Cu increases with time. The
 195 reproducibility of this trend was checked by conducting three individual isothermal runs, that turned out consistent.
 196 If muons are trapped only at vacancy associated sites, the result indicates that the number density of vacancies
 197 *increases* with time after quenching when all elements Mg, Si and Cu are present in the alloy composition. This
 198 suggests that new vacancies are continuously diffusing into the material and binding to solute atoms, shifting the

199 equilibrium concentration of vacancies to higher levels than in the alloys with fewer elements. For this to be possible,
200 vacancy–solute bonds must be much more energetically favorable to form in 1.0MS0.2Cu than in 1.6MS. As reported
201 in literature, Cu has the largest binding energy with vacancies among the solute elements and an attractive interaction
202 with Mg atoms [26, 28, 30-32]. Since the effect does not occur in binary Al–Cu, several elements must interact,
203 which suggests that also small vacancy-rich clusters (containing at least 2–3 solute atoms) can trap vacancies at 280
204 K (7 °C). Depending on the role of Si, a similar increase in vacancy concentration might also happen in ternary Al–
205 Mg–Cu alloys, which have not been studied with μ SR yet.

206 The early cluster formation kinetics in Al-Mg-Si alloys are slow in the presence of Cu [26], such that the clusters in
207 Al–Mg–Si–Cu alloys, stay small in size for a long time at room temperature. This means a higher density of clusters
208 in Cu-added alloys, and a higher tendency to contain vacancies. Meanwhile, clusters in Al–Mg–Si grow large and do
209 not bind vacancies as well, a behavior that can be prevented with short pre-aging treatments at e.g. 343–373 K (70–
210 100 °C) after SHT [11, 16]. The presence of vacancies inside clusters can be crucial for a good aging response: when
211 clusters transform into crystalline precipitates during artificial aging, the vacancies are freed and can again act as
212 nucleation points for further clusters and precipitates.

213 Muon spin relaxation experiments were performed on an Al–Mg–Si–Cu alloy and ternary/binary references to
214 investigate the effect of Cu on Mg–Si-clustering kinetics. As we increase the sample temperature from 20 K to 300
215 K (from –253 °C to +27 °C), we probe defects of lower densities and higher binding muon trapping potentials,
216 starting with single atoms and going through small atomic clusters and vacancies bound in clusters/precipitates,
217 finally ending up at vacancy–solute pairs and small vacancy-rich clusters at room temperature. This enables us to
218 make the following observations:

- 219 • When quenching a binary aluminium alloy from solution heat treatment (SHT), most of the vacancies have
220 escaped from Al–Si and Al–Cu after a few days at room temperature, while Al–Mg retains vacancies until a
221 heat treatment at 473 K (200 °C) is conducted, due to stable Mg–vacancy bonds. Temperatures of 623 K
222 (350 °C) are required to anneal the vacancies out of Al–Mg–Si(–Cu) alloys.
- 223 • Natural aging has a negative effect on the strength response upon artificial aging of Al–Mg–Si alloys, but
224 this is prevented by adding Cu. Our results indicate that this is caused by the quick formation and growth of
225 atomic clusters and loss of quenched-in vacancies in Al–Mg–Si, while a high concentration of smaller, more
226 vacancy-rich clusters are produced in Al–Mg–Si–Cu.
- 227 • In Al–Mg–Si–Cu alloys (but not Al–Cu or Al–Mg–Si alloys), the vacancy concentration even increases
228 during room temperature storage, because very stable Mg–Cu–vacancy configurations raises the equilibrium
229 concentration of vacancies in the material. All the alloying elements (possibly except Si) must be present in
230 order for the binding energy with vacancies to be sufficient to produce this effect.

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235 References

- 236 1. A. Serizawa, S. Hirosawa and T. Sato, *Metallurgical and Materials Transactions A* 2008, vol. 39,
237 pp. 243-251.
- 238 2. F. De Geuser, W. Lefebvre and D. Blavette, *Philosophical Magazine Letters* 2006, vol. 86, pp. 227-
239 234.
- 240 3. K. Matsuda, A. Kawai, K. Watanabe, S. Lee, C.D. Marioara, S. Wenner, K. Nishimura, T.
241 Matsuzaki, N. Nunomura, T. Sato, R. Holmestad and S. Ikeno, *Mater Trans* 2017, vol. 58, pp. 167-175.
- 242 4. S. Wenner, C.D. Marioara, S.J. Andersen and R. Holmestad, *Int J Mater Res* 2012, vol. 103, pp.
243 948-954.
- 244 5. F.A. Martinsen, F.J.H. Ehlers, M. Torsæter and R. Holmestad, *Acta Mater* 2012, vol. 60, pp. 6091-
245 6101.
- 246 6. J. Banhart, C.S.T. Chang, Z. Liang, N. Wanderka, M.D.H. Lay and A.J. Hill, *Advanced*
247 *Engineering Materials* 2010, vol. 12, pp. 559-571.
- 248 7. D.J. Chakrabarti and D.E. Laughlin, *Progress in Materials Science* 2004, vol. 49, pp. 389-410.
- 249 8. K. Matsuda, S. Ikeno, Y. Uetani and T. Sato, *Metallurgical and Materials Transactions A* 2001,
250 vol. 32, pp. 1293-1299.
- 251 9. C.D. Marioara, S.J. Andersen, T.N. Stene, H. Hasting, J. Walmsley, A.T.J. Van Helvoort and R.
252 Holmestad, *Philos Mag* 2007, vol. 87, pp. 3385-3413.
- 253 10. J. Kim, E. Kobayashi and T. Sato, *Mater Trans* 2015, vol. 56, pp. 1771-1780.
- 254 11. J. Kim, E. Kobayashi and T. Sato, *Mater Trans* 2011, vol. 52, pp. 906-913.
- 255 12. P. Dumitraschkewitz, S.S.A. Gerstl, P.J. Uggowitzer, J.F. Löffler and S. Pogatscher, *Advanced*
256 *Engineering Materials* 2017, vol. 19, p. 1600668.
- 257 13. S. Wenner, R. Holmestad, K. Matsuda, K. Nishimura, T. Matsuzaki, D. Tomono, F.L. Pratt and
258 C.D. Marioara, *Phys Rev B* 2012, vol. 86.
- 259 14. A. Yaouanc and P.D. de Réotier: *Muon Spin Rotation, Relaxation, and Resonance: Applications*
260 *to Condensed Matter*. OUP Oxford, 2011.
- 261 15. T. Matsuzaki, K. Ishida, K. Nagamine, I. Watanabe, G.H. Eaton and W.G. Williams, *Nuclear*
262 *Instruments and Methods in Physics Research Section A: Accelerators, Spectrometers, Detectors and*
263 *Associated Equipment* 2001, vol. 465, pp. 365-383.
- 264 16. S. Wenner, K. Nishimura, K. Matsuda, T. Matsuzaki, D. Tomono, F.L. Pratt, C.D. Marioara and
265 R. Holmestad, *Acta Mater* 2013, vol. 61, pp. 6082-6092.
- 266 17. T. Hatano, Y. Suzuki, M. Doyama, Y.J. Uemura, T. Yamazaki and J.H. Brewer, *Hyperfine*
267 *Interactions* 1984, vol. 17, pp. 211-217.
- 268 18. E. Sato, T. Hatano, Y. Suzuki, M. Imafuku, M. Sunaga, M. Doyama, Y. Morozumi, T. Suzuki and
269 K. Nagamine, *Hyperfine Interactions* 1984, vol. 17, pp. 203-209.
- 270 19. R.S. Hayano, Y.J. Uemura, J. Imazato, N. Nishida, T. Yamazaki and R. Kubo, *Phys Rev B* 1979,
271 vol. 20, pp. 850-859.
- 272 20. A. Schenck: *Muon spin rotation spectroscopy*. Taylor and Francis Inc, Philadelphia, PA (USA),
273 1985.
- 274 21. T. Yamazaki, *Hyperfine Interactions* 1979, vol. 6, pp. 115-125.
- 275 22. R. Kadono, J. Imazato, T. Matsuzaki, K. Nishiyama, K. Nagamine, T. Yamazaki, D. Richter and
276 J.M. Welter, *Phys Rev B* 1989, vol. 39, pp. 23-41.
- 277 23. K. Nishimura, K. Matsuda, R. Komaki, N. Nunomura, S. Wenner, R. Holmestad, T. Matsuzaki, I.
278 Watanabe and F.L. Pratt, *Arch Metall Mater* 2015, vol. 60, pp. 925-929.
- 279 24. O. Hartmann, E. Karlsson, E. Wäckelgrd, R. Wäppling, D. Richter, R. Hempelmann and T.O.
280 Niinikoski, *Phys Rev B* 1988, vol. 37, pp. 4425-4440.

- 281 25. L. Ismer, M.S. Park, A. Janotti and C.G. Van de Walle, *Phys Rev B* 2009, vol. 80, p. 184110.
282 26. M. Liu and J. Banhart, *Materials Science and Engineering: A* 2016, vol. 658, pp. 238-245.
283 27. M. Werinos, H. Antrekowitsch, T. Ebner, R. Prillhofer, P.J. Uggowitzer and S. Pogatscher, *Mater*
284 *Design* 2016, vol. 107, pp. 257-268.
285 28. M.W. Zandbergen, Q. Xu, A. Cerezo and G.D.W. Smith, *Acta Mater* 2015, vol. 101, pp. 136-148.
286 29. W.J. Kossler, A.T. Fiory, W.F. Lankford, J. Lindemuth, K.G. Lynn, S. Mahajan, R.P. Minnich,
287 K.G. Petzinger and C.E. Stronach, *Physical Review Letters* 1978, vol. 41, pp. 1558-1561.
288 30. D. Hatakeyama, K. Nishimura, K. Matsuda, T. Namiki, S. Lee, N. Nunomura, T. Aida, T.
289 Matsuzaki, R. Holmestad, S. Wenner and C.D. Marioara, *Metallurgical and Materials Transactions A* 2018.
290 31. P. Lang, Y.V. Shan and E. Kozeschnik, *Materials Science Forum* 2014, vol. 794-796, pp. 963-970.
291 32. P. Lang, T. Weisz, M.R. Ahmadi, E. Povoden-Karadeniz, A. Falahati and E. Kozeschnik,
292 *Advanced Materials Research* 2014, vol. 922, pp. 406-411.
293 33. S. Wenner, K. Nishimura, K. Matsuda, T. Matsuzaki, D. Tomono, F.L. Pratt, C.D. Marioara and
294 R. Holmestad, *Metall Mater Trans A* 2014, vol. 45a, pp. 5777-5781.

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297 **Figures and tables**

298 Figure 1: Example muon spin relaxation spectra for sample 1.0MS0.2Cu, showing spin asymmetry as a function of
 299 time spent inside the sample before muon decay.

300 Figure 2: Best-fit trapping rates for relaxation spectra acquired at increasing temperatures from 20 K to 300 K
 301 (−253 °C to +27 °C). (a) The Al–Mg–Si(–Cu) alloy as quenched and aged at 623 K (350 °C), as well as binary (Al–
 302 Mg) and ternary (Al–Mg–Si) alloy samples for reference. (b) Al–Mg–Si(–Cu) samples thermally aged at 423 K
 303 (150 °C) and room temperature stored for 1 year. (c) Binary Al–Cu and Al–Si alloys, and pure aluminium.

304 Figure 3: Fitted trapping rates from isothermal relaxation spectra. Samples are quenched from SHT and kept at 280 K
 305 (7 °C) throughout the measurements. The trapping rates decrease with time for all alloys except the quaternary Al–
 306 Mg–Si–Cu alloy, which increases with time.

307 TABLE 1: All samples used in this work. The sample composition (Al balanced), heat treatment after SHT and
 308 abbreviated labels for the samples are listed. A reference is given in cases where the samples have been used in earlier
 309 publications. RT means room temperature; AQ denotes “as quenched.”

Composition (at. %)	Heat treatment	Label	Reference
1.07 % Mg, 0.53 % Si	~15 min @ RT	1.6MS-AQ	[16, 23]
"	1 year @ RT	1.6MS-1y	[23]
"	1000 min @ 423 K (150 °C)	1.6MS-150C	[16, 23, 33]
"	30 min @ 623 K (350 °C)	1.6MS-350C	[33]
0.66 % Mg, 0.33 % Si, 0.2 % Cu	~10 min @ RT	1.0MS0.2Cu-AQ	
"	1 year @ RT	1.0MS0.2Cu-1y	
"	1000 min @ 423 K (150 °C)	1.0MS0.2Cu-150C	
"	30 min @ 623 K (350 °C)	1.0MS0.2Cu-350C	
1.0 % Mg	7 days @ RT	1.0Mg-7d	
0.5 % Si	~15 min @ RT	0.5Si-AQ	[16]
"	12 days @ RT	0.5Si-12d	[16]
0.2 % Cu	~10 min @ RT	0.2Cu-AQ	
"	10 days @ RT	0.2Cu10d	
"	1000 min @ 373 K	0.2Cu-100C	

	(100 °C)		
Pure Al, 0.01 % trace elements	66 days @ RT	base Al	[16, 23, 33]

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